imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

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MCD44-14io1B

=

=

 $= 2 \times 1400 \text{ V}$

49 A

1.34 V

Thyristor \ Diode Module

Phase I	eg
---------	----

Part number

MCD44-14io1B

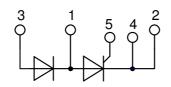


 V_{RRM}

I TAV

VT

Backside: isolated **E**72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

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Data according to IEC 60747and per semiconductor unless otherwise specified

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MCD44-14io1B

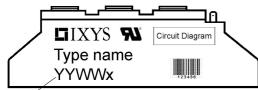
Rectifier					Ratings		!
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V _{RSM/DSM}	max. non-repetitive reverse/forwa	ard blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	١
V _{RRM/DRM}	max. repetitive reverse/forward b	locking voltage	$T_{vJ} = 25^{\circ}C$			1400	١
R/D	reverse current, drain current	$V_{R/D} = 1400 V$	$T_{VJ} = 25^{\circ}C$			100	μA
		$V_{R/D} = 1400 V$	$T_{vJ} = 125^{\circ}C$			5	m/
V _T	forward voltage drop	$I_{T} = 100 \text{ A}$	$T_{VJ} = 25^{\circ}C$			1.34	١
		$I_{T} = 200 \text{ A}$				1.75	١
		$I_{T} = 100 \text{ A}$	$T_{VJ} = 125 ^{\circ}C$			1.34	١
		I _T = 200 A				1.80	١
ITAV	average forward current	$T_c = 85^{\circ}C$	T _{vJ} = 125°C			49	ļ
T(RMS)	RMS forward current	180° sine				77	ļ
ν _{το}	threshold voltage		T _{v.I} = 125°C			0.85	١
r _T	slope resistance } for power le	oss calculation only				5.3	mΩ
R _{thJC}	thermal resistance junction to cas	Se .				0.53	K/W
R _{thCH}	thermal resistance case to heatsi				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$		0.20	180	W
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v_1} = 45^{\circ}C$			1.15	k/
• I SM		t = 8,3 ms; (60 Hz), sine	$V_{\rm N} = 0 V$			1.24	k/
		t = 0,0 ms; (50 Hz), sine	T _{v.i} = 125°C			980	4
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			1.06	, k/
12+	value for fusing	t = 10 ms; (50 Hz), sine	$V_{R} = 0 V$ $T_{VJ} = 45^{\circ}C$			6.62	
l²t	value for fushing		-				1
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$			6.40	kA ² s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 125 \circ C$			4.80	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_{\rm R} = 0 V$		54	4.63	kA ² s
C,	junction capacitance	$V_{R} = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		54		pF
P _{GM}	max. gate power dissipation	t _P = 30 μs	$T_c = 125^{\circ}C$			10	N
		$t_{P} = 300 \mu s$				5	N
P _{GAV}	average gate power dissipation					0.5	N
(di/dt) _{cr}	critical rate of rise of current		epetitive, $I_{T} = 150 \text{ A}$			150	A/μ
		t_{P} = 200 µs; di _G /dt =0.45 A/µs; -					
			on-repet., $I_{T} = 49 \text{ A}$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{vJ} = 125^{\circ}C$			1000	V/μ
		$R_{GK} = \infty$; method 1 (linear volta	ige rise)				
V _{gt}	gate trigger voltage	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			1.5	١
			$T_{vJ} = -40^{\circ}C$			1.6	١
I _{GT}	gate trigger current	$V_{D} = 6 V$	$T_{vJ} = 25^{\circ}C$			100	mÆ
			$T_{vJ} = -40^{\circ}C$			200	m/
V _{gd}	gate non-trigger voltage	$V_{\rm D} = \frac{2}{3} V_{\rm DBM}$	T _{vJ} = 125°C			0.2	١
I _{GD}	gate non-trigger current					10	mA
IL	latching current	t _p = 10 μs	$T_{vJ} = 25 ^{\circ}C$			450	m/
-	-	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$	-				
I _H	holding current	$V_{\rm D} = 6 \text{ V} \text{R}_{\rm GK} = \infty$	$T_{vJ} = 25 ^{\circ}\text{C}$			200	mA
т _{gd}	gate controlled delay time	$V_{\rm D} = \frac{1}{2} V_{\rm DRM}$	$T_{VJ} = 25 ^{\circ}\text{C}$			200	μ
• gd	gate controlled dolay line	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu\text{s}$				2	μ
	turn-off time	$V_{\rm R} = 100 \text{ V}; \ \text{I}_{\rm T} = 120 \text{ A}; \ \text{V} = \frac{3}{2}$			150		
t _q		$v_{2} = 100 V I_{2} = 170 A V = 7$			1:00		μ με

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MCD44-14io1B

Package	TO-240AA				F	Rating	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		125	°C
T _{op}	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface striking distance through ai		terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}			terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
		t = 1 minute	50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



Date Code

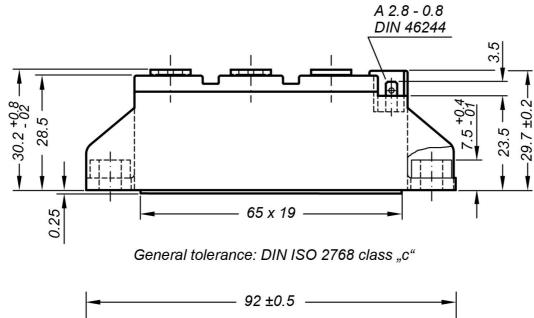
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD44-14io1B	MCD44-14io1B	Box	36	

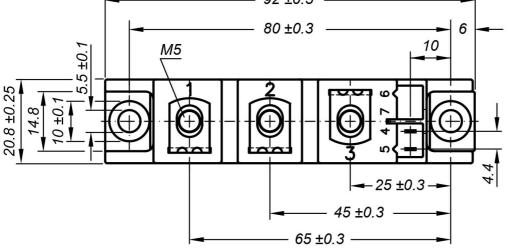
Similar Part	Package	Voltage class
MCMA50PD1600TB	TO-240AA-1B	1600
MCMA65PD1600TB	TO-240AA-1B	1600

Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 125 °C
	⊢R₀−	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$\mathbf{R}_{0 \max}$	slope resistance *	4.1		mΩ

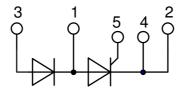
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Outlines TO-240AA





Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751 Type **ZY 200L** (L = Left for pin pair 4/5)



sin

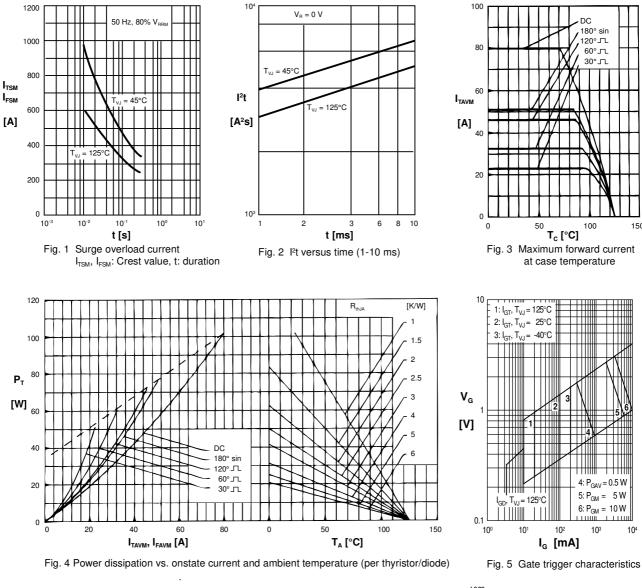
150

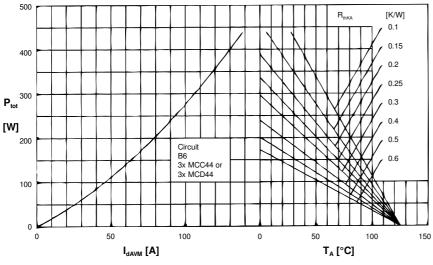
= 0.5 W

1.1.111

10

Thyristor





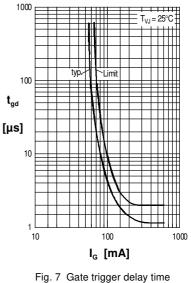


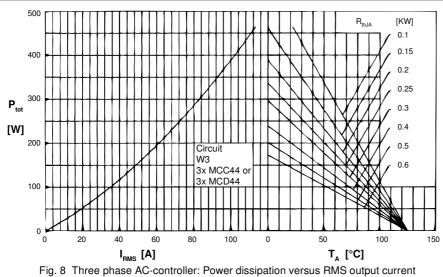
Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

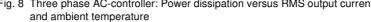
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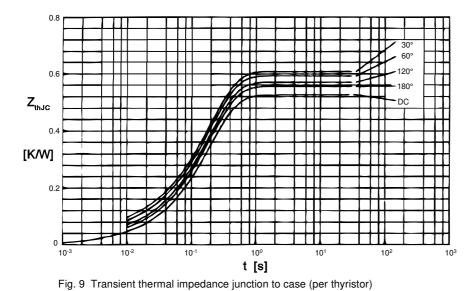
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MCD44-14io1B

Rectifier



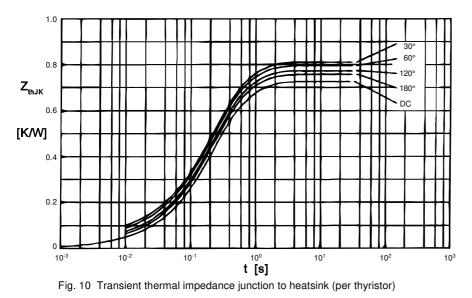




1100	,			
	d	R _{thJC} [K/W]		
	DC	0.53		
	180°	0.55		
	120°	0.58		
	60°	0.60		
	30°	0.62		
Constants for Z_{thJC} calculation:				
I I	R _{thi} [K/	W] t _i [s]		
1	0.01	5 0.0035		
2	0.02	6 0.0200		

 $\mathbf{R}_{_{thJC}}$ for various conduction angles d:

3	0.489	0.1950



${\rm R}_{_{thJK}}$ for various conduction angles d:						
	d R _u	_{лж} [K/W]				
	DC	0.73				
	180°	0.75				
	120°	0.78				
	60°	0.80				
	30°	0.82				
Со	Constants for Z _{thuk} calculation:					
i	R _{thi} [K/W] t _i [s]				
1	0.015	0.0035				
2	0.026	0.0200				
3	0.489	0.0195				
4	0.200	0.6800				

